NPN power transistor with integrated diode Rev. 01 — 29 July 2010

Product data sheet

Product profile 1.

1.1 General description

High voltage, high speed, planar passivated NPN power switching transistor with integrated anti-parallel emitter-collector diode in a SOT54 plastic package

1.2 Features and benefits

- Fast switching
- High typical DC current gain

1.3 Applications

- Compact fluorescent lamps (CFL)
- Low power electronic lighting ballasts

1.4 Quick reference data

- High voltage capability
- Integrated anti-parallel E-C diode
- Off-line self-oscillating power supplies (SOPS) for battery charging

Table 1.	Quick reference da	ata				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _C	collector current	DC	-	-	1.5	А
P _{tot}	total power dissipation	T _{lead} ≤ 25 °C; see <u>Figure 1</u>	-	-	2.1	W
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V	-	-	700	V
Static cha	aracteristics					
h _{FE}	DC current gain	$I_{C} = 0.5 \text{ A}; V_{CE} = 2 \text{ V};$ $T_{j} = 25 \text{ °C}$	8	17	25	



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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		_
2	С	collector		c L
3	E	emitter		B E sym131
			SOT54 (TO-92)	

3. Ordering information

Table 3. Ordering	g information		
Type number	Package		
	Name	Description	Version
PHD13003C	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54

4. Limiting values

Table 4.Limiting values

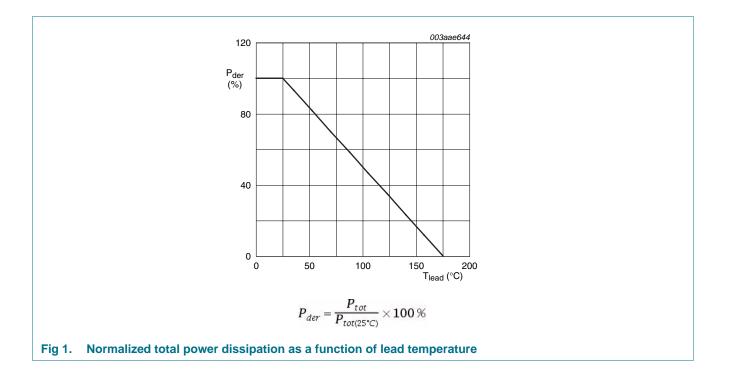
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CESM}	collector-emitter peak voltage	$V_{BE} = 0 V$	-	700	V
V _{CBO}	collector-base voltage	I _E = 0 A	-	700	V
V _{CEO}	collector-emitter voltage	$I_{B} = 0 A$	-	400	V
I _C	collector current	DC	-	1.5	А
I _{CM}	peak collector current		-	3	А
I _B	base current	DC	-	0.75	А
I _{BM}	peak base current		-	1.5	А
P _{tot}	total power dissipation	T _{lead} ≤ 25 °C; see <u>Figure 1</u>	-	2.1	W
T _{stg}	storage temperature		-65	150	°C
Tj	junction temperature		-	150	°C
V _{EBO}	emitter-base voltage	$I_{C} = 0 \text{ A}$; I(Emitter) = 10 mA	-	9	V

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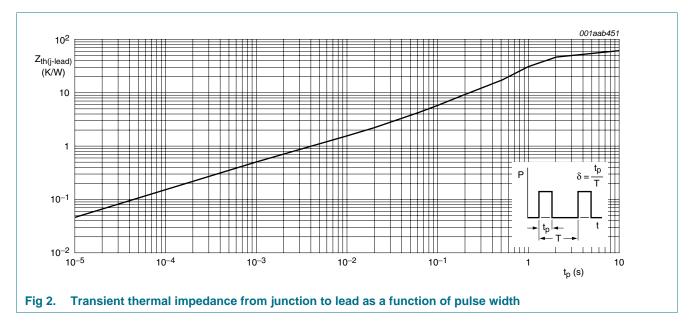
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5. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-lead)}$	thermal resistance from junction to lead	see Figure 2	-	-	60	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air; printed-circuit board mounted; lead length = 4 mm	-	150	-	K/W



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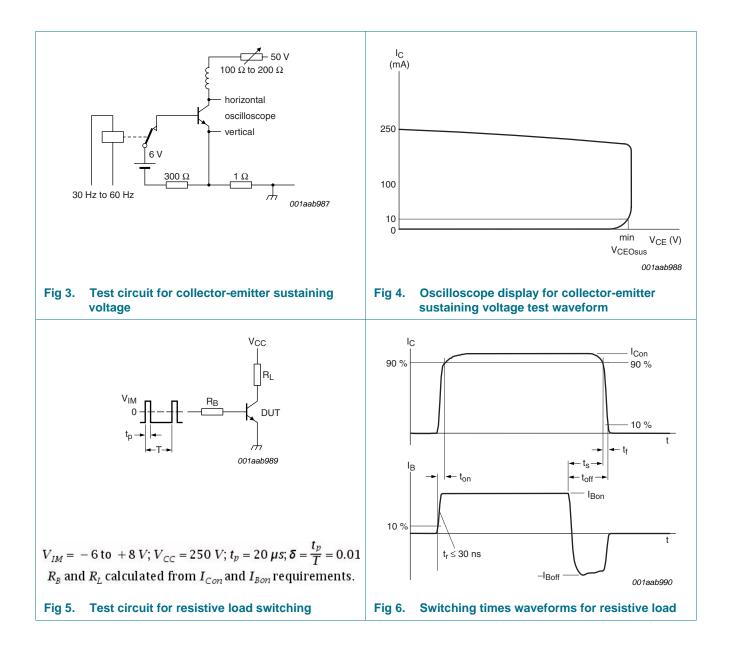
6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
I _{CES}	collector-emitter cut-off	$V_{BE} = 0 V; V_{CE} = 700 V$	-	-	1	mA
	current	$V_{BE} = 0 \text{ V}; V_{CE} = 700 \text{ V}; T_j = 100 \text{ °C}$	-	-	5	mA
I _{CEO}	collector-emitter cut-off current	V_{CE} = 400 V; I _B = 0 A; T _{lead} = 25 °C	-	-	0.1	mA
I _{EBO}	emitter-base cut-off current	V_{EB} = 9 V; I_C = 0 A; T_{lead} = 25 °C	-	-	1	mA
V _{CEOsus}	collector-emitter sustaining voltage	I _B = 0 A; I _C = 1 mA; L _C = 25 mH; T _{lead} = 25 °C; see <u>Figure 3</u> ; see <u>Figure 4</u>	400	-	-	V
V _{CEsat}	collector-emitter	$I_{C} = 0.5 \text{ A}; I_{B} = 0.1 \text{ A}; T_{lead} = 25 \text{ °C}$	-	-	0.5	V
	saturation voltage	I_{C} = 1 A; I_{B} = 0.25 A; T_{lead} = 25 °C	-	-	1	V
		$I_{C} = 1.5 \text{ A}; I_{B} = 0.5 \text{ A}; T_{lead} = 25 ^{\circ}\text{C}$	-	-	1.5	V
V _{BEsat}	base-emitter saturation voltage	I_{C} = 0.5 A; I_{B} = 0.1 A; T_{lead} = 25 °C	-	-	1	V
		I_{C} = 1 A; I_{B} = 0.25 A; T_{lead} = 25 °C	-	-	1.2	V
V _F	forward voltage	I _F = 0.5 A; T _j = 25 °C	-	-	1.5	V
h _{FE}	DC current gain	$I_{C} = 0.5 \text{ A}; V_{CE} = 2 \text{ V}; T_{j} = 25 \text{ °C}$	8	17	25	
		I_{C} = 1 A; V_{CE} = 2 V; T_{j} = 25 °C	5	9	15	
Dynamic	characteristics					
t _{on}	turn-on time	$I_{C} = 1 \text{ A}; I_{Bon} = 0.2 \text{ A}; I_{Boff} = -0.2 \text{ A};$	-	-	1	μs
t _s	storage time	$R_L = 75 \Omega$; $T_{lead} = 25 °C$; resistive load; see <u>Figure 5</u> ; see <u>Figure 6</u>	-	-	4	μs
		$\begin{split} I_{C} &= 1 \text{ A}; I_{Bon} = 0.2 \text{ A}; V_{BB} = -5 \text{ V}; \\ L_{B} &= 1 \mu\text{H}; T_{lead} = 25 ^\circ\text{C}; \text{ inductive load}; \\ \text{see } \underline{\text{Figure 7}}; \text{ see } \underline{\text{Figure 8}} \end{split}$	-	0.8	-	μs
t _f	fall time	$\begin{split} I_{C} &= 1 \text{ A}; I_{Bon} = 0.2 \text{ A}; I_{Boff} = -0.2 \text{ A}; \\ R_{L} &= 75 \Omega; T_{lead} = 25 ^{\circ}\text{C}; \text{ resistive load}; \\ \text{see } \underline{\text{Figure 5}}; \text{ see } \underline{\text{Figure 6}} \end{split}$	-	-	0.7	μs
		$\begin{split} I_{C} &= 0.5 \text{ A}; \ I_{Bon} = 0.1 \text{ A}; \ V_{BB} = -5 \text{ V}; \\ L_{B} &= 1 \mu\text{H}; \ T_{lead} = 25 \text{ °C}; \ \text{inductive load}; \\ \text{see Figure 7}; \ \text{see Figure 8} \end{split}$	-	0.1	-	μs

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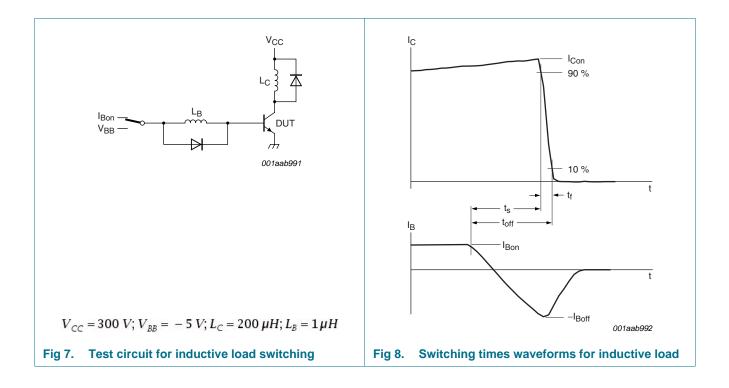
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7. Package outline

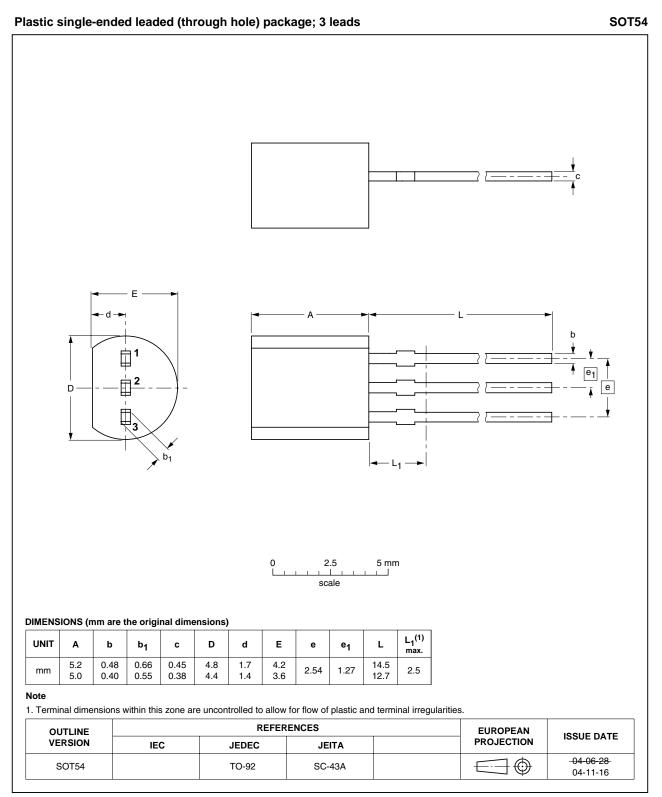


Fig 9. Package outline SOT54 (TO-92)

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8. Revision history

Table 7. Revision history					
Document ID	Release date	Data sheet status	Change notice	Supersedes	
PHD13003C v.1	20100729	Product data sheet	-	-	

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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